

Table of Contents

Preface

Anisotropic Acceptors Induced In GaAs by Group I Elements Cu, Ag, Au: Properties and Trends A.A. Gutkin	13
3D-4D-5D Transition and 4f Rare Earth Elements in III-V and II-VI Semiconductors as Luminescent Centres and Probes in Diagnostics of Implanted Layers V.V. Ushakov and A.A. Gippius	25
Symmetry of $V_{Ga}Te_{As}$ Complex in GaAs and its Reorientation at Low Temperature N.S. Averkiev, A.A. Gutkin, E.B. Osipov, M.A. Reshchikov and V.R. Sosnovskij	31
Electrodipole Spin Transitions of the Neutral Manganese Acceptor Mn^0_{Ga} in Gallium Arsenide N.P. Baran, V.Y. Bratus, V.M. Maksimenko, A.V. Markov and Y.G. Semenov	39
On the Ground State of Mn_{Ga} Defects in a GaAs: Mn System S.M. Yakubenya and K.F. Shtel'makh	45
Defect-Impurity Interaction in Irradiated n-GaAs F.P. Korshunov, T.A. Prokhorenko, N.A. Sobolev and E.A. Kudriavtseva	51
Long-Range Effect of Ion Irradiation on the System of Defects in Indium Phosphide N.V. Baidus, B.I. Bednyi, T.V. Belich and D.I. Tetelbaum	57
Phonon-Impurity Photoconductivity Due to Ge Acceptor in $GaAs_{1-x}Sb_x$ Alloys T.Y. Bilgildeyeve, T.A. Polyanskaya, A.A. Kopylov and A.A. Shakmaev	61
The EL2 Center in GaAs: Symmetry and Metastability N.T. Bagraev	67
Metastable Electronic States Caused by Native Defects and III-d Group Impurities in A^4B^6 Semiconductors B.A. Akimov and L.I. Ryabova	85
Electric Field Induced Electron Emission from Deep Level Center in GaAs E.A. Bobrova, G.N. Galkin, E.I. Ivanov, T.B. Papkova and S.G. Stapeev	105
Generation of the EL2 Defect in n-GaAs Irradiated by High Energy Protons P.N. Brunkov, S.G. Konnikov and M.M. Sobolev	111
Synergetic Photoelectric Phenomena Induced by Associations of Rare-Earth Metal Impurities with Lattice Defects in Si and Semiconductors of Type A_3B_5 and A_2B_6 P.M. Karageorgy-Alkalaev, A.Y. Leiderman and S.Z. Karazhanov	119
Peculiarities of Display of Multistable Defects in Relaxation Spectroscopy V.M. Siratskii, M.G. Sosnin, V.I. Shakhovtsov, V.L. Shindich, L.I. Shpinar and I.I. Yaskovets	125
Spectroscopy of II-VI Compounds Doped with Transition-Metal Ions A.I. Ryskin	133
Photoionization of the Impurity Ion in ZnS:Fe: Influence of Lattice Relaxation Y.B. Rosenfeld, A.I. Ryskin, A.V. Vasil'ev and G.M. Zinger	143
Vibronic Interaction and Luminescence of ZnSe:Cr A.I. Ryskin, A.V. Vasil'ev, V.A. Kremerman and Y.B. Rosenfeld	149
Quenching Centers of Red Luminescence in ZnSe:Te G. Račiukaitis, V. Gavryushin, A. Kazlauskas, V.D. Ryzhikov, R. Baltramiejunas and D. Juodžbalis	157
Dynamics of Electron-Phonon Interaction in ZnSe:Cr Crystals under Photoexcitation in Charge Transfer Band M.P. Bulany, I.I. Jeru, V.Y. Ivanov, A.P. Stepanenko and Y.E. Zaly	163
Nonlinear Spectroscopy of DA-Centers of Green-Edge-Luminescence in CdS Crystals. Stepwise Exciton Localization by Isoelectronic Defects R. Baltramiejunas, V. Gavryushin, V. Kubertavicius and G. Račiukaitis	169
Superfine Splitting in CdS Doped by Fe R.P. Vardapetyan, V.D. Kuznetsov, V.A. Kulbachinskii, S.I. Reyman, I.V. Svistunov and S.M. Chudinov	175
Peculiarities of Spin-Splitting in the Exciton Spectra of $Cd_{1-x}Mn_xS$ Crystals in a Magnetic Field V.G. Abramishvili, A.V. Komarov, S.M. Ryabchenko and Y.G. Semenov	181

Exitonic Spectra of $\text{Cd}_{1-x}\text{Fe}_x\text{Te}$ Crystals S.A. Permogorov, L.N. Tenishev and T.P. Surkova	187
Energy States of Ni in $\text{Zn}_{1-x}\text{Mn}_x\text{Se:Ni}$ Solid Solutions S.A. Permogorov, L.N. Tenishev, V.I. Sokolov and T.P. Surkova	193
Non-Equilibrium Diffusion in Silicon N.T. Bagraev, L.E. Klyachkin and V.L. Sukhanov	201
Non-Equilibrium Phenomena during Impurity Diffusion in Heavily Doped Silicon A.O. Konstantinov	215
Diffusion of Gold in Single Crystal Silicon with Growth Microdefects V.V. Vysotskaya and S.N. Gorin	221
Enhanced Gold Diffusion in Silicon under Intrinsic Point Defect Flow S.V. Koveshnikov, E.B. Yakimov and N. Yarykin	227
Impurity Diffusion in Silicon under Strong Interaction with the Point Defect Clusters V.I. Pashkov, V.A. Perevoshchikov and V.D. Skupov	239
Mechanisms of Impurity Diffusion into $\text{Pb}_{1-x}\text{Sn}_x\text{Te}$ Solid Solution J.B. Chesnokova and C. Chor	243
The Effect of Abnormal Ion Electromigration in a Disorder Media D. Alimov, V. Goldman and B. Oksengendler	249
H States and Passivation of Defects and Impurities in Silicon B.N. Mukashev and S.Z. Tokmoldin	255
Electron Stimulated Defect Reactions in Silicon under Pulsed Photon Treatment V.I. Belyavsky, Y.A. Kapustin and V.V. Sviridov	265
Piezocapacitance Spectroscopy of Deep Level Centers in Silicon A.A. Lebedev, W. Ecke and N.A. Sultanov	273
Deep Levels of Thermal Defects in High Resistivity Silicon E. Verbitskaya, A.A. Gribov, V. Eremin, A.M. Ivanov and N.B. Strokan	277
Capacitance Transient Spectroscopy of Process-Induced Defects with Deep Levels in P-Type Silicon E.V. Astrova, V.B. Voronkov and A.A. Lebedev	283
Radiation Defect Formation in Silicon Doped with Impurities of the Group IV Transition Metals L.A. Kazakevich, V.I. Kuznetsov, P.F. Lugakov and A.R. Salmanov	287
Influence Intrinsic Elastic Stresses on the Annealing Processes of Radiation Defects in Silicon L.I. Khirunenko, Y.V. Pomozev, V.I. Shakhovtsov, V.K. Shinkarenko and V.I. Yashnik	293
Thermal Broadening of the Absorption Lines of Group III and V Elements in Single-Crystal Silicon N.I. Agladze, A.S. Kaminskii and A.N. Safonov	299
Interstitial Oxygen in Nature and Monoisotopic Germanium F.M. Vorobkalo, L.I. Khirunenko, V.I. Shakhovtsov and V.K. Shinkarenko	305
Defect Production in Si:Ge Irradiated by Gamma-Rays at 4.2K, 78K and 300K V.V. Emtsev, V.G. Golubev, P.M. Klinger, G.I. Kropotov and Y.V. Shmartsev	311
The Substitutional Reaction in Alloys $\text{Si}_{1-x}\text{Ge}_x$ B. Askarov, B. Oksengendler, S. Sokhataliyev, M. Khaitova and A. Yusupov	317
The Defects in Germanium-Silicon Alloys S.I. Shakhovtsova and M.M. Shvarts	323
The Influence of Current Carriers on Shallow Impurity Limited Solubility in Semiconductors I.G. Atabaev	329
New Shape of Inhomogeneously Broadened Resonance Lines in Semi-Infinite Media: Luminescence of Sm^{2+} Ions in Thin Epitaxial CaF_2 Films on Si (111) N.S. Averkiev, V.S. Vikhnin, N.S. Sokolov and N.L. Yakovlev	335
Hopping Conductivity of Ion-Implanted by Sulphur Silicon V.A. Kulbachinskii, V.G. Kytin, A.N. Timofeyev, A.G. Uliashin, V.V. Abramov, G.A. Mironova and N.V. Shlopak	341
Method and Model for Treating Negative-U Centers in Silicon: Si:V^0 and $\text{Si:}(\text{VH}_3)^-$ S.S. Moliver	349

Zn-Related Center in Silicon: Negative-U Properties N.T. Bagraev and I.S. Polovtsev	367
Resonance (Quasilocal) States in A^{IV}B^{VI} Semiconductors V.I. Kaidanov	387
Superconductivity in IV-VI Semiconductors Induced by Impurity Resonance States V.I. Kaidanov, S.A. Nemov, A.V. Berezin, M.K. Zhitinskaya, R.V. Parfeniev and D. Shamshur	407
The Self-Comensation of Electrical Active Impurity by Intrinsic Defects in Solid Solutions Pb_{0.8}Sn_{0.2}Te and Pb_{0.93}Sn_{0.07}Se S.A. Nemov, V.I. Proshin, M.K. Zhitinskaya and Y.I. Ravich	417
Tunnel Spectroscopy of Resonance and Metastable Impurity States in Lead Telluride V.I. Kaidanov and S.A. Rykov	421
PbTe(Ga) Photoconductivity Spectra in the Far Infrared A.I. Belogorokhov, I.I. Ivanchik, D.R. Khokhlov and E.I. Slynko	433
Low-Temperature Switching in PbTe<Ga> at High Electric Fields B.A. Akimov, A.V. Albul and E.V. Bogdanov	437
Localization in Ultrahigh Magnetic Fields in the Pb_{1-x}Sn_xTe (In) Alloys I.I. Ivanchik, D.R. Khokhlov, A. de Visser and A.V. Nikorich	443
Microwave Resonance of the Persistent Photoconductivity in Pb_{1-x}Sn_xTe(In) Alloys S.N. Chesnokov, D.E. Dolzhenko, I.I. Ivanchik and D.R. Khokhlov	449
Electrical and Photoelectrical Properties of PbSnTe/PbTeS Lattice Matched Heterostructure Diodes V.V. Tetyorkin, F.F. Sizov, V.B. Alenberg, S.N. Davidenko and V.Y. Chopik	453
Dislocations in Semiconductors as One Dimensional Electronic Systems V.V. Kveder	461
Dislocation Superlattices Based on Lead Chalcogenides as HTSC Models O.A. Mironov, V.V. Zorchenko, A.Y. Sipatov, A.I. Fedorenko, O.N. Nashchekina and S.V. Chistyakov	473
Metastable Behavior of Dislocation Charge in Space Charge Region E.B. Yakimov and N. Yarykin	485
Possibility of Reconstruction of Concentration Profile of Point Defects in Crystals by the Method of X-Ray Interference Diffractometry T.E. Goureev, A. Nikulin, P.V. Petrashen and A.A. Snigirev	491
Anomalously Wide Impurity Atmosphere near the Dislocation Slip Plane in Si V.G. Eremenko and O.V. Trofimov	497
Oxygen-Related Thermal Donors in Heat-Treated Cz-Si V.V. Emtsev, G.A. Oganessian and K. Schmalz	505
Formation and Properties of Thermal Donors Generated by Prolonged Annealing in Si Crystals with Different Oxygen and Carbon Contents V.M. Babich, N.P. Baran, A.A. Bugai, V.B. Kovalchuk, V.M. Maksimenko and B.D. Shanina	517
Metastability of Thermal Donors in Silicon: Photo-EPR Study N.T. Bagraev	529
Peculiarities of Thermal Donors Generation and Oxygen Precipitation at 650°C with Silicon Irradiated by Neutrons V.B. Nejmarsh, Y.V. Pomezov, V.I. Shakhovtsov, A.N. Cabaldin, L.R. Malko and V.M. Tsmots	537
Thermal Donor Formation Affected by Strain Fields Induced by Imperfections of Silicon Crystal Lattice I.I. Kolkovskii, P.F. Lugakov, V.V. Lukyanitsa and A.V. Tsikunov	543
Analytical Approach to the Theory of Transition-Metal Impurities in Semiconductors N.P. Il'in and V.F. Masterov	551
Cluster Approach for Investigation of Semiconductor Crystals D.E. Onopko and A.I. Ryskin	565
Structure of Deep Impurity States of II, III, IV Group Elements in IV-VI Semiconductors V.S. Vinogradov	571
Coexistence of Large and Small Radius Electron States on Defect and Problem of Charge Photo-Transfer in Ruby V.S. Vikhnin	579
Two-Level Correlated Model for Recombination in γ,e-Irradiated Silicon S.M. Dickmann	587

Fluctuation-Slow-Interface-Traps B.I. Fouks	595
Surface Coulomb Traps B.I. Fouks and N.M. Storonskii	603
Impurity Polarizability in Silicon Due to the Magnetic Degeneracy of Donor States in a Finite Magnetic Field S.M. Dickmann and D.I. Sidel'nikov	611
New Ideas Concerning the Nitrogen Donor States in Noncubic SiC Basing on the High-Resolution EPR Data B.D. Shanina, E.N. Kalabukhova, S.N. Lukin and E.N. Mokhov	619
Definition of the Off-Center Positions Coordinates of Boron in 6H SiC from High-Resolution EPR Spectra B.D. Shanina, E.N. Kalabukhova, S.N. Lukin and E.N. Mokhov	627
EPR and DLTS of Point Defects in Silicon Carbide Crystals V.A. Il'in and V.S. Ballandovich	633
Electronic Structure of Boron in Silicon Carbide V.Y. Bratus, N.P. Baran, A.A. Bugai, A.A. Klimov, V.M. Maksimenko, T.L. Petrenko and V. Romanenko	645
EPR of the Antisite Defect in Epitaxial Layers of 4H SiC E.N. Kalabukhova, S.N. Lukin, E.N. Mokhov and B.D. Shanina	655
Electron Structure of ^{11}B Impurity in 6H SiC Crystal Measured by Endor T.L. Petrenko, V.V. Teslenko and E.N. Mokhov	661
Models of Impurity Boron in Various SiC Polytypes T.L. Petrenko, V.V. Teslenko and E.N. Mokhov	667
Radiative and Radiationless Recombination Processes in 6H and 4H SiC Diodes and the Effect of Deep Centres M.M. Anikin, A.A. Lebedev and A.M. Strel'chuk	673